

Application No.: 10/055,320
Filing Date: January 23, 2002
Inventor: Neil J. Basson et al.
Response Dated: September 3, 2004
Reply to Office Action of June 3, 2004

Remarks/Arguments

Record of Substance of Examiner Interview

Applicants thank the Examiners for courtesies rendered in the August 5th, 2004 telephone interview. To comply with the requirement of 37 CFR 1.133, applicants set forth below a record of the substance of the interview.

1. No exhibits were shown and no demonstrations were conducted.
2. All claims were discussed.
3. US Pat. No. 6,261,850 was discussed.
4. Applicants' proposed action is described on the Examiner's Interview Summary Form.
5. Applicants pointed out that US Pat. No. 6,261,850 teaches a way to lower the resistivity of deposit material, not to deposit a high resistivity, conductive material.
6. No other pertinent matters were discussed.
7. The general results of the interview are described on the Examiner's Interview Summary Form.

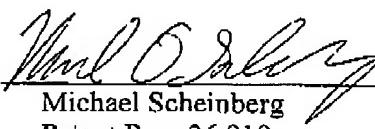
Declaration

Applicants attach a Declaration under 37 CFR 1.132 (mistakenly titled "Declaration under 37 CFR 1.32") which shows that the definition of the term "high resistivity" in the context of focused ion beam deposited materials would be understood by skilled persons. The Declaration also addresses the resistivity of structures deposited in accordance with the teaching of US Pat. No. 6,261,850.

Respectfully submitted,

Date: 9/3/04

By:


Michael Scheinberg
Patent Reg. 36,919
P.O. Box 164140
Austin, Texas 78716-4140